Reinforced, Fast, Low-Power, Two-Channel Digital Isolators

MAX22290/MAX22291

Product Highlights

- **AEC-Q100 Qualification for /V Devices**
- Reinforced Galvanic Isolation for Digital Signals
  - 8-SOIC with 4mm of Creepage and Clearance
  - Withstands $3kV_{RMS}$ for 60s (V_{ISO})
  - Continuously withstands $445V_{RMS}$ (V_{IOWM})
  - Withstands ±10kV Surge between GNDA and GNDB with 1.2/50μs Waveform
  - High CMTI (50kV/μs, typ)
- Low Power Consumption
  - 0.78mW per Channel at 1Mbps with $V_{DD\_}$ = 1.8V
  - 1.47mW per Channel at 1Mbps with $V_{DD\_}$ = 3.3V
  - 3.28mW per Channel at 100Mbps with $V_{DD\_}$ = 1.8V
- Low Propagation Delay and Low Jitter
  - Up to 200Mbps Maximum Data Rate
  - Low Propagation Delay 7ns (typ) at $V_{DD\_}$ = 3.3V
  - Clock Jitter RMS 7.5ps (typ)
- Safety Regulatory Approvals
  - UL According to UL1577
  - cUL According to CSA Bulletin 5A
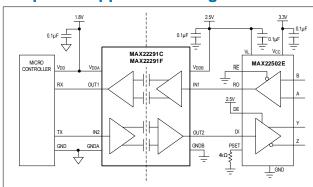 - VDE 0884-11 Reinforced Insulation (Pending)

Key Applications

- Automotive
  - Hybrid Electric Vehicle
  - Chargers
  - Battery Management Systems (BMS)
  - Inverters

The MAX22290/MAX22291 is a family of 2-channel reinforced, fast, low-power digital galvanic isolators using Maxim's proprietary process technology. All devices feature reinforced isolation for a withstand voltage rating of $3kV_{RMS}$ for 60 seconds. Both automotive and general-purpose devices are rated for operation at ambient temperatures of -40°C to +125°C.
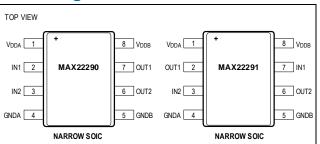
Devices with /V suffix are AEC-Q100 qualified. See the *Ordering Information* table for all automotive grade part numbers.

- Industrial
  - Isolated SPI
  - Isolated RS-232, RS-485/RS-422, CAN
  - Fieldbus Communications
  - Motor Drive

Simplified Application Diagram

Pin Configurations

These devices transfer digital signals between circuits with different power domains, using as little as 0.78mW per channel at 1Mbps (1.8V supply). The low-power feature reduces system dissipation, increases reliability, and enables compact designs.

The devices are available with a maximum data rate of 25Mbps or 200Mbps, and with outputs that are either default high or default low. They feature low propagation delay and low clock jitter, which reduces system latency.

Independent 1.71V to 5.5V supplies on each side of the isolator also make the devices suitable for use as level translators.

The MAX22290 features two channels transferring data in the same direction. The two channels of the MAX22291 transfer data in opposite directions, and this makes the MAX22291 ideal for isolating the Tx and Rx lines of a transceiver.

Ordering Information appears at end of data sheet.

19-101159; Rev 2; 10/21

Absolute Maximum Ratings

V_{DDA} to GNDA ....-0.3V to +6V

V_{DDB} to GNDB ....-0.3V to +6V

IN_ on Side A to GNDA ....-0.3V to +6V

IN_ on Side B to GNDB ....-0.3V to +6V

OUT_ on Side A to GNDA .... -0.3V to (V_{DDA} + 0.3V)

OUT_ on Side B to GNDB .... -0.3V to (V_{DDB} + 0.3V)

Short-Circuit Continuous Current

   OUT_ on Side A to GNDA .... ±30mA

OUT_ on Side B to GNDB... ±30mA

Continuous Power Dissipation (T_A = +70°C)

   Narrow SOIC (derate 5.79mW/°C above +70°C)... 462.96mW

Temperature Ratings

   Operating Temperature Range......................-40°C to +125°C

   Maximum Junction Temperature ....+150°C

   Storage Temperature Range.........................-60°C to +150°C

   Lead Temperature (soldering, 10s) ....+300°C

   Soldering Temperature (reflow)...................................+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Information

8 NARROW SOIC

Package Code	S8MS+24
Outline Number	*21-0041*
Land Pattern Number	*90-0096*
THERMAL RESISTANCE, FOUR-LAYER BOARD	
Junction-to-Ambient (θ_{JA})	172.8°C/W
Junction-to-Case Thermal Resistance (θ_{JC})	67.6°C/W

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to *www.maximintegrated.com/thermal-tutorial*.

For the latest package outline information and land patterns (footprints), go to *www.maximintegrated.com/packages*. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Electrical Characteristics

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (Notes 1, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
SUPPLY VOLTAGE							
Supply Voltage	V_{DDA}	Relative to GNDA		1.71		5.5	V
	V_{DDB}	Relative to GNDB		1.71		5.5	
Undervoltage-Lockout Threshold	$V_{UVLO\_}$	$V_{DD\_}$ rising		1.5	1.6	1.66	V
Undervoltage-Lockout Threshold Hysteresis	V_{UVLO_HYST}				45		mV
MAX22290 SUPPLY CURRENT (Note 2)							
Side A Supply Current	I_{DDA}	500kHz square wave, C_L = 0pF	V_{DDA} = 5V		0.31	0.57	mA
			V_{DDA} = 3.3V		0.30	0.56	
			V_{DDA} = 2.5V		0.30	0.56	
			V_{DDA} = 1.8V		0.29	0.41	
		50MHz square wave, C_L = 0pF	V_{DDA} = 5V		2.38	3.25	
			V_{DDA} = 3.3V		2.32	3.18	
			V_{DDA} = 2.5V		2.29	3.14	
			V_{DDA} = 1.8V		2.22	2.89	
Side B Supply Current	I_{DDB}	500kHz square wave, C_L = 0pF	V_{DDB} = 5V		0.60	1.11	mA
			V_{DDB} = 3.3V		0.59	1.10	
			V_{DDB} = 2.5V		0.59	1.09	
			V_{DDB} = 1.8V		0.58	1.06	
		50MHz square wave, C_L = 0pF	V_{DDB} = 5V		3.02	3.80	
			V_{DDB} = 3.3V		2.12	2.80	
			V_{DDB} = 2.5V		1.74	2.35	
			V_{DDB} = 1.8V		1.42	1.95	
MAX22291 SUPPLY CURRENT (Note 2)							
Side A Supply Current	I_{DDA}	500kHz square wave, C_L = 0pF	V_{DDA} = 5V		0.46	0.84	mA
			V_{DDA} = 3.3V		0.45	0.83	
			V_{DDA} = 2.5V		0.44	0.83	
			V_{DDA} = 1.8V		0.44	0.74	
		50MHz square wave, C_L = 0pF	V_{DDA} = 5V		2.65	3.50	
			V_{DDA} = 3.3V		2.18	2.95	
			V_{DDA} = 2.5V		1.98	2.72	
			V_{DDA} = 1.8V		1.80	2.40	
Side B Supply Current	I_{DDB}	500kHz square wave, C_L = 0pF	V_{DDB} = 5V		0.46	0.84	mA
			V_{DDB} = 3.3V		0.45	0.83	
			V_{DDB} = 2.5V		0.44	0.83	
			V_{DDB} = 1.8V		0.44	0.74	
		50MHz square wave, C_L = 0pF	V_{DDB} = 5V		2.65	3.50	
			V_{DDB} = 3.3V		2.18	2.95	

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (Notes 1, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
			V_{DDB} = 2.5V		1.98	2.72	
			V_{DDB} = 1.8V		1.80	2.40	
LOGIC INTERFACE (IN_, OUT_)							
Input High Voltage	V_{IH}	2.25V ≤ $V_{DD\_}$ ≤ 5.5V		0.7 x V_{DD}			V
		1.71V ≤ $V_{DD\_}$ < 2.25V		0.75 x V_{DD}			
Input Low Voltage	V_{IL}	2.25V ≤ $V_{DD\_}$ ≤ 5.5V				0.8	V
		1.71V ≤ $V_{DD\_}$ < 2.25V				0.7	
Input Hysteresis	V_{HYS}	MAX2229_B/E			410		mV
		MAX2229_C/F			80		
Input Pullup Current	I_{PU}	MAX2229_B/C		-10	-5	-1.5	µA
Input Pulldown Current	I_{PD}	MAX2229_E/F		1.5	5	10	µA
Input Capacitance	C_{IN}	f_{SW} = 1MHz			2		pF
Output Voltage High	V_{OH}	I_{OUT} = -4mA source		$V_{DD\_}$ - 0.4			V
Output Voltage Low	V_{OL}	I_{OUT} = 4mA sink				0.4	V

Dynamic Characteristics MAX2229_C/F

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (Notes 2, 4)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	CMTI	IN_ = GND_ or $V_{DD\_}$ (Note 5)			50		kV/µs
Maximum Data Rate	DR_{MAX}	2.25V ≤ $V_{DD\_}$ ≤ 5.5V		200			Mbps
		1.71V ≤ $V_{DD\_}$ < 2.25V		150			
Minimum Pulse Width	PW_{MIN}	2.25V ≤ $V_{DD\_}$ ≤ 5.5V				5	ns
		1.71V ≤ $V_{DD\_}$ < 2.25V				6.67	
Propagation Delay (*Figure 1*)	t_{PLH}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	4.4	6.2	9.5	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	4.8	7.0	11.2	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	5.3	8.3	14.7	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	7.1	12.3	22.1	
	t_{PHL}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	4.6	6.5	9.9	
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	5.0	7.3	11.6	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	5.4	8.5	14.9	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	7.2	12.1	21.8	
Pulse Width Distortion	PWD	|t_{PLH} - t_{PHL}|	4.5V ≤ $V_{DD\_}$ ≤ 5.5V		0.4	2	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V		0.4	2	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V		0.3	2	

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (Notes 2, 4)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V			0.0	2	
Propagation Delay Skew Part-to-Part (Same Channel)	t_{SPLH}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				3.7	ns
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				4.7	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				6.9	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				12.1	
	t_{SPHL}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				4.0	
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				4.9	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				7.0	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				11.8	
Propagation Delay Skew Channel-to-Channel (Same Direction) (*Figure 1*)	t_{SCSLH}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				2	ns
	t_{SCSHL}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				2	
Propagation Delay Skew Channel-to-Channel (Opposite Direction)	t_{SCOLH}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				2	ns
	t_{SCOHL}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				2	
Peak Eye Diagram Jitter	$t_{JIT(PK)}$	200Mbps			100		ps
Clock Jitter RMS	$t_{JCLK(RMS)}$	500kHz clock input, rising/falling edges			7.5		ps
Rise Time (*Figure 1*)	t_R	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			0.8	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.1	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.5	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V			2.4	
Fall Time (*Figure 1*)	t_F	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			1	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.4	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.9	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V			3	

Dynamic Characteristics MAX2229_B/E

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (Notes 2, 4)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	CMTI	IN_ = GND_ or $V_{DD\_}$ (Note 5)			50		kV/µs
Maximum Data Rate	DR_{MAX}			25			Mbps
Minimum Pulse Width	PW_{MIN}					40	ns
Glitch Rejection				10	17	29	ns
Propagation Delay (*Figure 1*)	t_{PLH}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	16.7	22.6	30.7	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	17.0	23.4	32.2	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	17.7	24.8	35.3	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	19.6	28.8	42.8	
	t_{PHL}	IN_ to OUT_, C_L = 15pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V	16.4	22.7	32.1	
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V	16.8	23.5	33.8	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V	17.3	24.8	36.7	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V	19.0	28.4	43.7	
Pulse Width Distortion	PWD	$|t_{PLH} - t_{PHL}|$	4.5V ≤ $V_{DD\_}$ ≤ 5.5V		0.1	4	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V		0.1	4	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V		0.0	4	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V		0.4	4	
Propagation Delay Skew Part-to-Part (Same Channel)	t_{SPLH}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				14.0	ns
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				13.8	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				15.2	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				21.9	
	t_{SPHL}	4.5V ≤ $V_{DD\_}$ ≤ 5.5V				13.0	
		3.0V ≤ $V_{DD\_}$ ≤ 3.6V				13.5	
		2.25V ≤ $V_{DD\_}$ ≤ 2.75V				15.4	
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				21.4	
Propagation Delay Skew Channel-to-Channel (Same Direction) (*Figure 1*)	t_{SCSLH}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				4	ns
	t_{SCSHL}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				4	
Propagation Delay Skew Channel-to-Channel (Opposite Direction)	t_{SCOLH}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				4	ns
	t_{SCOHL}	1.71V ≤ $V_{DD\_}$ ≤ 5.5V				4	
Peak Eye Diagram Jitter	$t_{JIT(PK)}$	25Mbps				250	ps
Rise Time (*Figure 1*)	t_R	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			0.8	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.1	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.5	

(V_{DDA} - V_{GNDA} = 1.71V to 5.5V, V_{DDB} - V_{GNDB} = 1.71V to 5.5V, C_L = 15pF, T_A = -40°C to +125°C, unless otherwise noted. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.) (Notes 2, 4)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
		1.71V ≤ $V_{DD\_}$ ≤ 1.89V				2.4	
Fall Time (*Figure 1*)	t_F	C_L = 5pF	4.5V ≤ $V_{DD\_}$ ≤ 5.5V			1	ns
			3.0V ≤ $V_{DD\_}$ ≤ 3.6V			1.4	
			2.25V ≤ $V_{DD\_}$ ≤ 2.75V			1.9	
			1.71V ≤ $V_{DD\_}$ ≤ 1.89V			3	

Note 1: General purpose devices are 100% production tested at T_A = +25°C. Specifications over temperature are guaranteed by design and characterization. Automotive devices are 100% production tested at T_A = +25°C and T_A = +125°C.

Note 2: Not production tested. Guaranteed by design and characterization.

Note 3: All currents into the device are positive. All currents out of the device are negative. All voltages are referenced to their respective ground (GNDA or GNDB), unless otherwise noted.

Note 4: All measurements taken with V_{DDA} = V_{DDB}, unless otherwise noted.

Note 5: CMTI is the maximum sustainable common-mode voltage slew rate while maintaining the correct output. CMTI applies to both rising and falling common-mode voltage edges. Tested with the transient generator connected between GNDA and GNDB (V_{CM} = 1000V).

ESD Protection

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
ESD		Human Body Model All Pins		±3		kV
		IEC 61000-4-2 Contact, GNDB to GNDA		±6		

Test Circuit and Timing Diagram
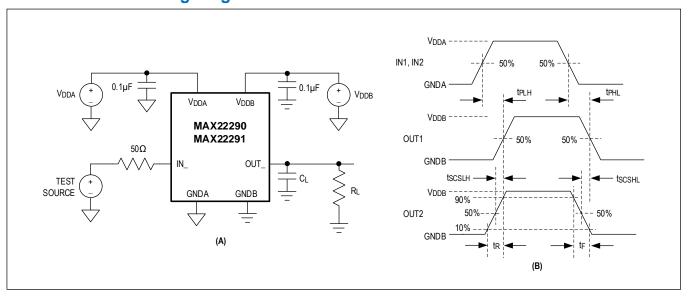

Figure 1. Test Circuit (A) and Timing Diagram (B)

Table 1. Insulation Characteristics

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS
Partial Discharge Test Voltage	V_{PR}	Method B1 = V_{IORM} x 1.875 (t = 1s, partial discharge < 5pC)	1182	V_P
Maximum Repetitive Peak Isolation Voltage	V_{IORM}	(Note 6)	630	V_P
Maximum Working Isolation Voltage	V_{IOWM}	Continuous RMS voltage (Note 6)	445	V_{RMS}
Maximum Transient Isolation Voltage	V_{IOTM}	t = 1s (Note 6)	4242	V_P
Maximum Withstanding Isolation Voltage	V_{ISO}	f_{SW} = 60Hz, duration = 60s (Notes 6, 7)	3000	V_{RMS}
Maximum Surge Isolation Voltage	V_{IOSM}	Reinforced Insulation, test method per IEC 60065, V_{TEST} = 1.6 x V_{IOSM} = 10000V_{PEAK} (Notes 6, 9)	6250	V_P
Isolation Resistance	R_{IO}	V_{IO} = 500V, T_A = 25°C	> 10^{12}	Ω
		V_{IO} = 500V, 100°C ≤ T_A ≤ 125°C	> 10^{11}	
		V_{IO} = 500V, T_S = 150°C	> 10^9	
Barrier Capacitance Side A to Side B	C_{IO}	f_{SW} = 1MHz (Note 8)	1.5	pF
Minimum Creepage Distance	CPG		4	mm
Minimum Clearance Distance	CLR		4	mm
Internal Clearance		Distance through insulation	0.021	mm
Comparative Tracking Index	CTI	Material Group II (IEC 60112)	> 400	
Climate Category			40/125/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	

Note 6: V_{ISO}, V_{IOTM}, V_{IOWM}, V_{IORM} and V_{IOSM} are defined by the IEC 60747-5-5 standard.
Note 7: Product is qualified at V_{ISO} for 60s and 100% production tested at 120% of V_{ISO} for 1s.
Note 8: Capacitance is measured with all pins on field-side and logic-side tied together.
Note 9: Devices are immersed in oil during surge characterization.

Safety Regulatory Approvals

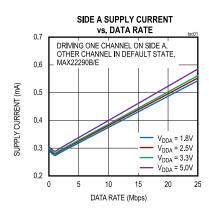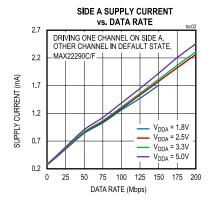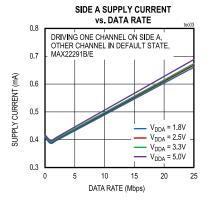| UL |
| --- |
| The MAX22290/MAX22291 are certified under UL1577. For more details, refer to File E351759. |
| Rated up to 3000V$_{RMS}$ isolation voltage for single protection. |
| **cUL (Equivalent to CSA notice 5A)** |
| The MAX22290/MAX22291 are certified up to 3000V$_{RMS}$ for single protection. For more details, refer to File E351759. |
| **VDE (Pending)** |
| The MAX22290/MAX22291 are certified to DIN VDE V 0884-11: 2017-1. Reinforced Insulation, Maximum Transient Isolation Voltage 4242V$_{PK}$, Maximum Repetitive Peak Isolation Voltage 630V$_{PK}$. |

These couplers are suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
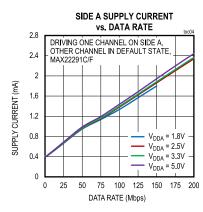
Typical Operating Characteristics

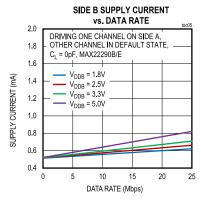(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)

(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)

SIDE B SUPPLY CURRENT vs. DATA RATE

toc07

DRIVING ONE CHANNEL ON SIDE A,
OTHER CHANNEL IN DEFAULT STATE,
C_L = 0pF, MAX22290C/F

- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SIDE B SUPPLY CURRENT vs. DATA RATE

toc08

DRIVING ONE CHANNEL ON SIDE A,
OTHER CHANNEL IN DEFAULT STATE,
C_L = 15pF, MAX22290C/F

- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SIDE B SUPPLY CURRENT vs. DATA RATE

toc09

DRIVING ONE CHANNEL ON SIDE A,
OTHER CHANNEL IN DEFAULT STATE,
C_L = 0pF, MAX22291B/E

- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SIDE B SUPPLY CURRENT vs. DATA RATE

toc10

DRIVING ONE CHANNEL ON SIDE A,
OTHER CHANNEL IN DEFAULT STATE,
C_L = 15pF, MAX22291B/E

- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SIDE B SUPPLY CURRENT vs. DATA RATE

toc11

DRIVING ONE CHANNEL ON SIDE A,
OTHER CHANNEL IN DEFAULT STATE,
C_L = 0pF, MAX22291C/F

- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

SIDE B SUPPLY CURRENT vs. DATA RATE

toc12

DRIVING ONE CHANNEL ON SIDE A,
OTHER CHANNEL IN DEFAULT STATE,
C_L = 15pF, MAX22291C/F

- V_{DDB} = 1.8V
- V_{DDB} = 2.5V
- V_{DDB} = 3.3V
- V_{DDB} = 5.0V

PROPAGATION DELAY vs. TEMPERATURE

toc13

V_{DDA} = V_{DDB}
IN_ TO OUT_, t_{PLH}
MAX2229_B/E

- $V_{DD\_}$ = 1.8V
- $V_{DD\_}$ = 2.5V
- $V_{DD\_}$ = 3.3V
- $V_{DD\_}$ = 5.0V

PROPAGATION DELAY vs. TEMPERATURE

toc14

V_{DDA} = V_{DDB}
IN_ TO OUT_, t_{PLH}
MAX2229_C/F

- $V_{DD\_}$ = 1.8V
- $V_{DD\_}$ = 2.5V
- $V_{DD\_}$ = 3.3V
- $V_{DD\_}$ = 5.0V

PROPAGATION DELAY vs. V_{DDA} VOLTAGE

toc15

V_{DDB} = 3.3V
IN_ TO OUT_, t_{PLH}

MAX2229_B/E

MAX2229_C/F

(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)
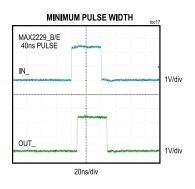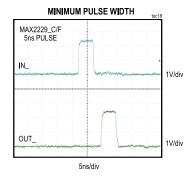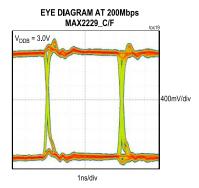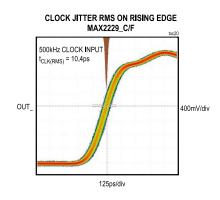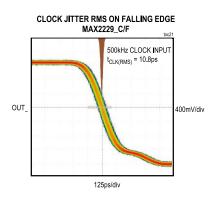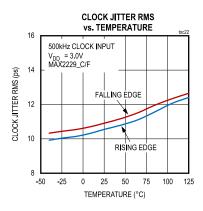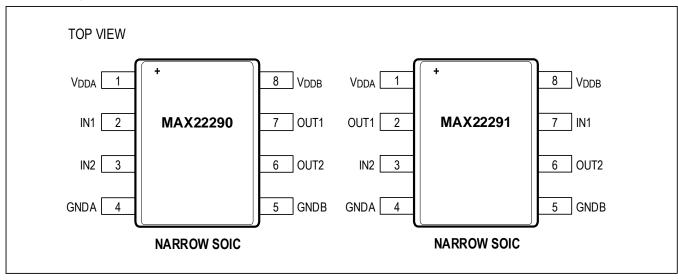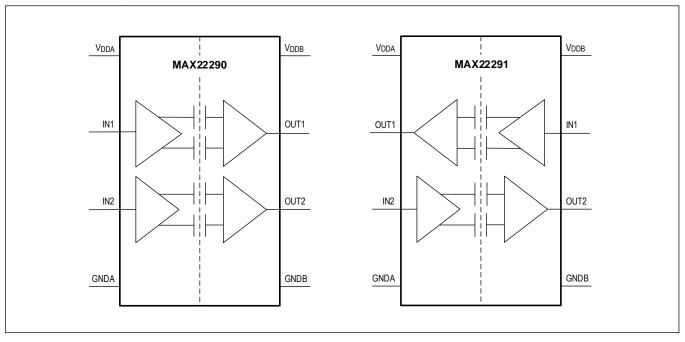
PROPAGATION DELAY vs. V_{DDB} VOLTAGE
toc16

V_{DDA} = 3.3V
IN_ TO OUT_, t_{PLH}

MAX2229_B/E

MAX2229_C/F

MINIMUM PULSE WIDTH
toc17

MAX2229_B/E
40ns PULSE

IN_   1V/div

OUT_   1V/div

20ns/div

MINIMUM PULSE WIDTH
toc18

MAX2229_C/F
5ns PULSE

IN_   1V/div

OUT_   1V/div

5ns/div

EYE DIAGRAM AT 200Mbps
MAX2229_C/F
toc19

V_{DDB} = 3.0V

400mV/div

1ns/div

CLOCK JITTER RMS ON RISING EDGE
MAX2229_C/F
toc20

500kHz CLOCK INPUT
$t_{CLK(RMS)}$ = 10.4ps

OUT_   400mV/div

125ps/div

CLOCK JITTER RMS ON FALLING EDGE
MAX2229_C/F
toc21

500kHz CLOCK INPUT
$t_{CLK(RMS)}$ = 10.8ps

OUT_   400mV/div

125ps/div

CLOCK JITTER RMS vs. TEMPERATURE
toc22

500kHz CLOCK INPUT
V_{DD} = 3.0V
MAX2229_C/F

FALLING EDGE

RISING EDGE

Pin Configurations

TOP VIEW

V_{DDA} 1 | MAX22290 | 8 V_{DDB}

IN1 2 | 7 OUT1

IN2 3 | 6 OUT2

GNDA 4 | 5 GNDB

NARROW SOIC

V_{DDA} 1 | MAX22291 | 8 V_{DDB}

OUT1 2 | 7 IN1

IN2 3 | 6 OUT2

GNDA 4 | 5 GNDB

NARROW SOIC

Pin Description

PIN		NAME	FUNCTION
MAX22290	MAX22291		
1	1	V_{DDA}	Power Supply Input for Side A. Bypass V_{DDA} to GNDA with a 0.1µF ceramic capacitor as close as possible to the pin.
2	—	IN1	Logic Input 1 on Side A
—	2	OUT1	Logic Output 1 on Side A
3	3	IN2	Logic Input 2 on Side A
4	4	GNDA	Ground Reference for Side A
5	5	GNDB	Ground Reference for Side B
6	6	OUT2	Logic Output 2 on Side B
7	—	OUT1	Logic Output 1 on Side B
—	7	IN1	Logic Input 1 on Side B
8	8	V_{DDB}	Power Supply Input for Side B. Bypass V_{DDB} to GNDB with a 0.1µF ceramic capacitor as close as possible to the pin.

Functional Diagrams

Detailed Description

The MAX22290/MAX22291 is a family of 2-channel reinforced digital isolators. The devices have an isolation rating of $3kV_{RMS}$. The MAX22290/MAX22291 family offers two unidirectional channel configurations to accommodate any 2-channel design.

The MAX22290 features two channels transferring digital signals in one direction for applications such as isolated digital I/O. The MAX22291 has one channel to transmit data in one direction and the other channel to transmit in the opposite direction, making it ideal for applications such as isolated RS232 or RS485 communication.

The devices are available in an 8-pin narrow-body SOIC package with 4mm creepage and clearance and are rated up to $3kV_{RMS}$. This family of digital isolators offers the low-power operation, high electromagnetic interference (EMI) immunity, and stable temperature performance through Maxim's proprietary process technology. The devices isolate different ground domains and block high-voltage/high-current transients from sensitive or human interface circuitry.

The devices are available with a maximum data rate of either 25Mbps (B/E versions) or 200Mbps (C/F versions). The MAX2229_B/C feature default-high outputs. The MAX2229_E/F feature default-low outputs. The default is the state the output assumes when the input is not powered or if the input is an open circuit. The devices have two supply inputs (V_{DDA} and V_{DDB}) that independently set the logic levels on either side of the device. V_{DDA} and V_{DDB} are referenced to GNDA and GNDB, respectively. The MAX22290/MAX22291 family also features a refresh circuit to ensure output accuracy when an input remains in the same state indefinitely.

Digital Isolation

The MAX22290/MAX22291 provide reinforced galvanic isolation for digital signals that are transmitted between two ground domains. The devices withstand differences of up to $3kV_{RMS}$ for up to 60 seconds, and up to $630V_{PEAK}$ of continuous isolation.

AEC-Q100 Qualification

Devices with /V suffix are AEC-Q100 qualified. See the *Ordering Information* table for all automotive grade part numbers.

Level Shifting

The wide supply voltage range of both V_{DDA} and V_{DDB} allows the devices to be used for level translation in addition to isolation. V_{DDA} and V_{DDB} can be independently set to any voltage from 1.71V to 5.5V. The supply voltage sets the logic level on the corresponding side of the isolator.

Unidirectional Channels

Each channel of these devices is unidirectional; it only passes data in one direction, as indicated in the *Functional Diagrams*. Each device features two unidirectional channels that operate independently with guaranteed data rates from DC up to 25Mbps (B/E versions), or from DC to 200Mbps (C/F versions). The output driver of each channel is push-pull, eliminating the need for pullup resistors. The outputs can drive both TTL and CMOS logic inputs.

Startup and Undervoltage Lockout

The V_{DDA} and V_{DDB} supplies are both internally monitored for undervoltage conditions. Undervoltage events can occur during power-up, power-down, or during normal operation due to a sagging supply voltage. When an undervoltage condition is detected on either supply, all outputs go to their default states regardless of the state of the inputs as seen in *Table 2*. *Figure 2*–*Figure 5* shows the behavior of the outputs during power-up and power-down.

Table 2. MAX22290/MAX22291 Output Behavior During Undervoltage Condition

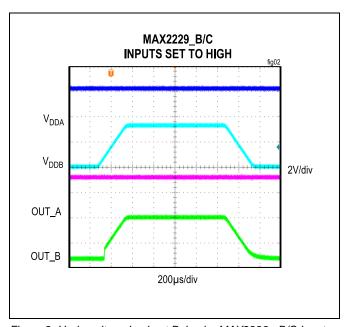| $V_{IN\_}$	V_{DDA}	V_{DDB}	V_{OUTA}	V_{OUTB}
1	Powered	Powered	High	High
0	Powered	Powered	Low	Low
X	Undervoltage	Powered	Default	Default
X	Powered	Undervoltage	Default	Default

Figure 2. Undervoltage Lockout Behavior MAX2229_ B/C Input High
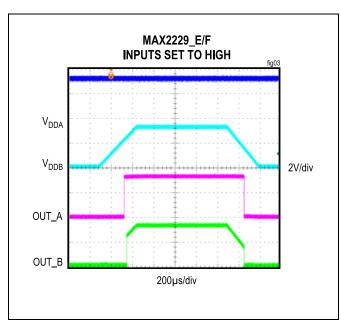

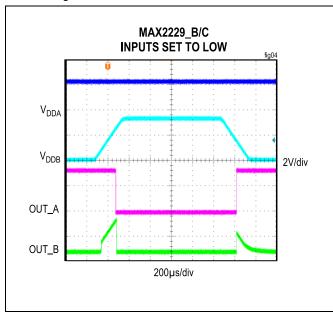Figure 3. Undervoltage Lockout Behavior MAX2229_ E/F Input High

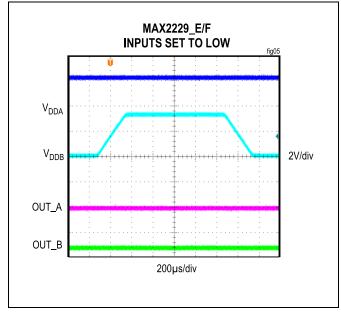Figure 4. Undervoltage Lockout Behavior MAX2229_ B/C Input Low

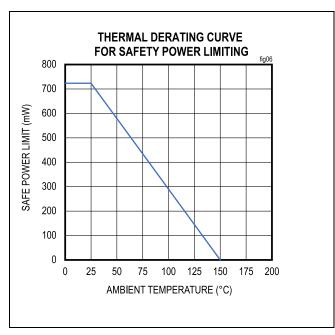Figure 5. Undervoltage Lockout Behavior MAX2229_ E/F Input Low

Safety Limits

Damage to the IC can result in a low-resistance path to the ground or to the supply and, without current limiting, the MAX22290/MAX22291 can dissipate excessive amounts of power. Excessive power dissipation can damage the die and result in damage to the isolation barrier, potentially causing downstream issues. *Table 3* shows the safety limits for the MAX22290/MAX22291.

The maximum safety temperature (T_S) for the device is the 150°C maximum junction temperature specified in the *Absolute Maximum Ratings*. The power dissipation (P_D) and junction-to-ambient thermal impedance (θ_{JA}) determine the junction temperature. Thermal impedance values (θ_{JA} and θ_{JC}) are available in the *Package Information* section and power dissipation calculations are discussed in the *Calculating Power Dissipation* section. Calculate the junction temperature (T_J) as:

$$T_J = T_A + (P_D \times \theta_{JA})$$

Figure 6 and *Figure 7* show the thermal derating curves for safety limiting the power and the current of the devices. Ensure that the junction temperature does not exceed 150°C.
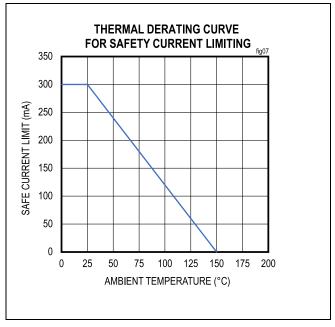
Figure 6. Thermal Derating Curve for Safety Power Limiting

Figure 7. Thermal Derating Curve for Safety Current Limiting

Table 3.   Safety Limiting Values for the MAX22290/MAX22291

PARAMETER	SYMBOL	TEST CONDITIONS	MAX	UNIT
Safety Current on Any Pin (No Damage to Isolation Barrier)	I_S	$T_J = 150°C$, $T_A = 25°C$	300	mA
Total Safety Power Dissipation	P_S	$T_J = 150°C$, $T_A = 25°C$	723.38	mW
Maximum Safety Temperature	T_S		150	°C

Applications Information

Power-Supply Sequencing

The MAX22290/MAX22291 do not require special power-supply sequencing. The logic levels are set independently on either side by V_{DDA} and V_{DDB}. Each supply can be present over the entire specified range regardless of the level or presence of the other supply.

Power-Supply Decoupling

To reduce ripple and the chance of introducing data errors, bypass V_{DDA} and V_{DDB} with 0.1µF low-ESR ceramic capacitors to GNDA and GNDB, respectively. Place the bypass capacitors as close to the power-supply input pins as possible.

Layout Considerations

The PCB designer should follow some critical recommendations to get the best performance from the design.

- Keep the input/output traces as short as possible. To keep signal paths low inductance, avoid using vias.
- Have a solid ground plane underneath the high-speed signal layer.
- Keep the area underneath the MAX22290/MAX22291 free from ground and signal planes. Any galvanic or metallic connection between Side A and Side B defeats the isolation.

Calculating Power Dissipation

The required current for a given supply (V_{DDA} or V_{DDB}) can be estimated by summing the current required for each channel.

The supply current for a channel depends on whether the channel is an input or an output, the channel's data rate, and the capacitive or resistive load if it is an output. The typical current for input or output at any data rate can be estimated from the graphs in *Figure 8* and *Figure 9*. Note that the data in *Figure 8* and *Figure 9* are extrapolated from the supply current measurements in a typical operating condition.

The total current for a single channel is the sum of the no-load current (shown in *Figure 8* and *Figure 9*), which is a function of voltage and data rate, and the load current, which depends on the type of load. Current into a capacitive load is a function of the load capacitance, the switching frequency, and the supply voltage.

$$I_{CL} = C_L \times f_{SW} \times V_{DD}$$

where:

I_{CL} is the current required to drive the capacitive load.

C_L is the load capacitance on the isolator's output pin.

f_{SW} is the switching frequency (bits per second/2).

V_{DD} is the supply voltage on the output side of the isolator.

Current into a resistive load depends on the load resistance, the supply voltage, and the average duty cycle of the data waveform. The DC load current can be conservatively estimated by assuming the output is always high.

$$I_{RL} = V_{DD} \div R_L$$

where:

I_{RL} is the current required to drive the resistive load.

V_{DD} is the supply voltage on the output side of the isolator.

R_L is the load resistance on the isolator's output pin.

Example (shown in *Figure 10*): A MAX22291C/F is operating with V_{DDA} = 2.5V, V_{DDB} = 3.3V, channel 1 operating at 100Mbps with a 15pF capacitive load, and channel 2 operating at 20Mbps and 50% duty cycle with a 10kΩ resistive load. See *Table 4* and *Table 5* for V_{DDA} and V_{DDB} supply-current calculation worksheets.
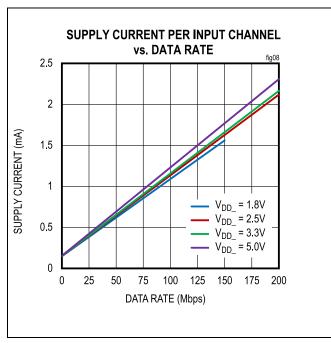
V$_{DDA}$ must supply:

- Channel 1 is an output channel operating at 2.5V and 100Mbps, consuming 0.84mA, estimated from *Figure 9*.
- Channel 2 is an input channel operating at 2.5V and 20Mbps, consuming 0.35mA, estimated from *Figure 8*.
- I$_{CL}$ on Channel 1 for 15pF capacitor at 2.5V and 100Mbps is 1.875mA.

Total current for side A = 0.84mA + 0.35mA + 1.875mA = 3.065mA (typ)

V$_{DDB}$ must supply:

- Channel 1 is an input channel operating at 3.3V and 100Mbps, consuming 1.16mA, estimated from *Figure 8*.
- Channel 2 is an output channel operating at 3.3V and 20Mbps, consuming 0.41mA, estimated from *Figure 9*.
- I$_{RL}$ on Channel 2 for 10kΩ resistor switching at 50% duty cycle and at 3.3V is 0.165mA.

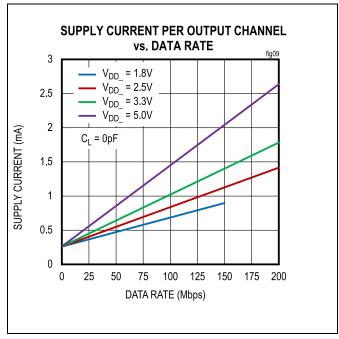Total current for side B = 1.16mA + 0.41mA + 0.165mA = 1.735mA (typ)
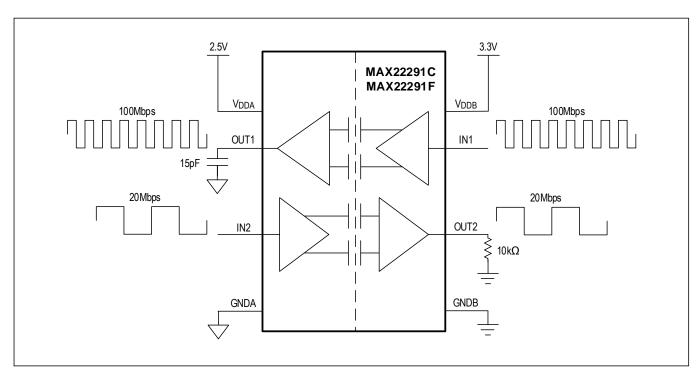

Figure 8. Supply Current per Input Channel (Estimated)

Figure 9. Supply Current per Output Channel (Estimated)

Figure 10. Example Circuit for Supply Current Calculation

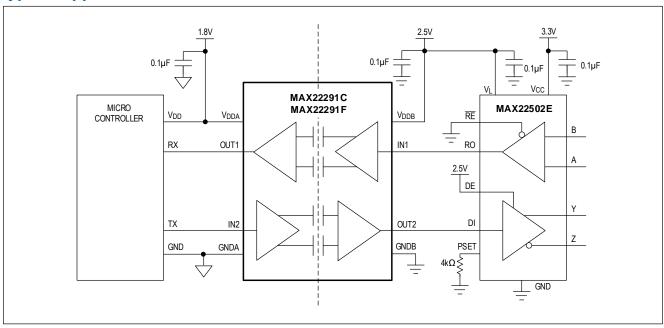## Table 4. Side A Supply Current Calculation Worksheet

SIDE A						$V_{DDA} = 2.5V$
CHANNEL	IN/OUT	DATA RATE (Mbps)	LOAD TYPE	LOAD	NO LOAD CURRENT (mA)	LOAD CURRENT (mA)
1	OUT	100	Capacitive	15pF	0.84	2.5V x 50MHz x 15pF = 1.875mA
2	IN	20			0.35	
Total: 3.065mA						

Table 5. Side B Supply Current Calculation Worksheet

SIDE B						$V_{DDB} = 3.3V$
CHANNEL	IN/OUT	DATA RATE (Mbps)	LOAD TYPE	LOAD	NO LOAD CURRENT (mA)	LOAD CURRENT (mA)
1	IN	100			1.16	
2	OUT	20	Resistive	10kΩ	0.41	3.3V / 10kΩ x 0.5 = 0.165mA
Total: 1.735mA						

Typical Application Circuits

Product Selector Guide

DEVICE CONFIGURATION	MAX DATA RATE	
	25Mbps	200Mbps
DEFAULT-HIGH OUTPUT	B	C
DEFAULT-LOW OUTPUT	E	F

Ordering Information

PART NUMBER	CHANNEL CONFIGURATION	DATA RATE (Mbps)	DEFAULT OUTPUT	ISOLATION VOLTAGE (kV$_{RMS}$)	TEMPERATURE RANGE	PIN-PACKAGE
GENERAL PURPOSE DEVICES						
MAX22290BASA+*	2/0	25	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22290CASA+*	2/0	200	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22290EASA+*	2/0	25	Low	3	-40°C to +125°C	8 Narrow SOIC
MAX22290FASA+*	2/0	200	Low	3	-40°C to +125°C	8 Narrow SOIC
MAX22291BASA+*	1/1	25	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22291CASA+*	1/1	200	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22291EASA+*	1/1	25	Low	3	-40°C to +125°C	8 Narrow SOIC
MAX22291FASA+*	1/1	200	Low	3	-40°C to +125°C	8 Narrow SOIC
AUTOMOTIVE DEVICES						
MAX22290BASA/V+*	2/0	25	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22290CASA/V+*	2/0	200	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22290EASA/V+*	2/0	25	Low	3	-40°C to +125°C	8 Narrow SOIC
MAX22290FASA/V+*	2/0	200	Low	3	-40°C to +125°C	8 Narrow SOIC
MAX22291BASA/V+*	1/1	25	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22291CASA/V+	1/1	200	High	3	-40°C to +125°C	8 Narrow SOIC
MAX22291EASA/V+	1/1	25	Low	3	-40°C to +125°C	8 Narrow SOIC
MAX22291FASA/V+*	1/1	200	Low	3	-40°C to +125°C	8 Narrow SOIC

*Future product—contact Maxim for availability.

+Denotes a lead(Pb)-free/RoHS-compliant package.

/V Denotes an automotive qualified part.

Chip Information

PROCESS: BiCMOS

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	07/21	Release for Market Intro	—
1	09/21	Added ESD Contact specification in ESD Protection table	7
2	10/21	Removed Pending from Safety Regulatory Approvals and added Pending after VDE 0884-11 in *Product Highlights*; removed Pending from UL and cUL in Safety Regulatory Approvals	1, 9